

Specification Amendments

Please amend the paragraph of page 7, lines 3-11 of the specification as follows.

-- Fig. 3 shows XRD results on the Cu_2Se thin film ~~grown~~ which is deposited and formed in step S102 on the InSe film formed in step S101. As can be seen, ~~the an~~ initial InSe thin film has been ~~changed to~~ covered by the Cu_2Se thin film. X-ray fluorescence spectroscopy (XRF) analysis confirms that In was not detected and that the second thin film was completely made of Cu_2Se . That is, when Cu was ~~grown~~ deposited on the InSe thin film by MOCVD using a (hfac)Cu(DMB) precursor, ~~original no In has disappeared and was replaced with Cu thus showing conversion~~ InSe layer was detectable. Rather, the XRD analysis showed the presence of Cu thus confirming coverage of the InSe layer into with the layer of Cu_2Se . --

Please amend the paragraph of page 7, lines 12-16 of the specification as follows.

-- Fig. 4 shows the XRD results on the CuInSe_2 thin film ~~grown~~ formed by conversion in step S103. As can be seen, XRD patterns of the grown CuInSe_2 thin film were consistent with those of a generally known CuInSe_2 single crystal. The ~~grown~~ CuInSe_2 thin film was shown to have a single phase of a tetragonal structure. --